Supporting Information

Magnetoresistance and Charge Transport in Graphene Governed by Nitrogen Dopants

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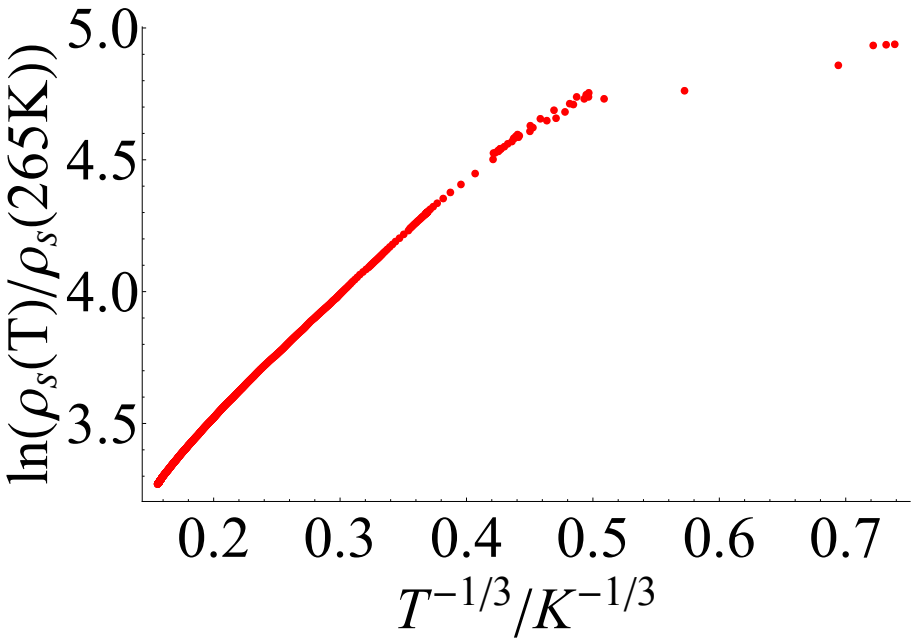

Figure S 1: Plot of the sheet resistance as function of temperature over the entire temperature range. While at high temperatures a clear exponential behavior is observed, a deviation can be seen at lower temperatures. Below ~8 K the resistance becomes logarithmic as expected for weak localization. From the exponential increase a transport gap of 9.1 meV can be estimated as described in the main manuscript.